

REVISION RECORD		
REV	DESCRIPTION	DATE
0	INITIAL RELEASE	03/06/03
A	• PAGE 3, CHANGED INITIAL RATE OF RADS TO 240 RADS/SEC	03/21/05
B	• PAGE 3, PARAGRAPH 3.7.1 CHANGED VERBIAGE.	05/06/08
C	• PAGE 12, CHANGED RH CANNED SAMPLE TABLE III FOR QUALIFYING DICE SALES ADDED TEMPERATURE CYCLE, CONSTANT ACCELERATION & REMOVED PIND TEST.	02/10/09
D	Page 2, amended section 3.3, <u>Special Handling of Dice</u> , to more accurately describe our current procedures and requirements.	04/05/12
E	Page 12, Changed RH Canned Sample Table for Qualifying Dice Sales: Subgroup 6 Sample Size Series changed from 45 (3) to 65 (3). First note had the Sample Size Series from "15%" to "10%".	07/02/13
F	Updated the Die Sales table on pg 12.	03/24/15
G	To remove SI and changed Linear Technology to Analog Devices	12/17/20
H	To remove Philippines	3/19/21

CAUTION: ELECTROSTATIC DISCHARGE SENSITIVE PART

REVISION	PAGE NO.	1	2	3	4	5	6	7	8	9	10	11	12				
INDEX	REVISION	F	F	F	F	F	F	F	F	F	F	F	F				
REVISION	PAGE NO.																
INDEX	REVISION																

										ANALOG DEVICES INC.							
		ORIG								TITLE: MICROCIRCUIT, LINEAR, RH101A OPERATIONAL AMPLIFIER DICE							
		DSGN															
		ENGR															
		MFG															
		CM															
		QA															
		PROG								SIZE	CAGE CODE	DRAWING NUMBER	REV				
											64155	05-08-5154	H				
APPLICATION	FUNCT	SIGNOFFS		DATE		CONTRACT:											

FOR OFFICIAL USE ONLY

1.0 SCOPE:

- 1.1 This specification defines the performance and test requirements for a microcircuit processed to a space level manufacturing flow.

2.0 APPLICABLE DOCUMENTS:

- 2.1 Government Specifications and Standards: the following documents listed in the Department of Defense Index of Specifications and Standards, of the issue in effect on the date of solicitation, form a part of this specification to the extent specified herein.

SPECIFICATIONS:

MIL-PRF-38535 Integrated Circuits (Microcircuits) Manufacturing, General Specification for

MIL-STD-883 Test Method and Procedures for Microcircuits

MIL-STD-1835 Microcircuits Case Outlines

- 2.2 Order of Precedence: In the event of a conflict between the documents referenced herein and the contents of this specification, the order of precedence shall be this specification, MIL-PRF-38535 and other referenced specifications.

3.0 REQUIREMENTS:

- 3.1 General Description: This specification details the requirements for the RH101A Operational Amplifier Dice and Element Evaluation Test Samples, processed to space level manufacturing flow as specified herein.

- 3.2 Part Number: **RH101A Dice**

- 3.3 **Special Handling of Dice:** Rad Hard dice require special handling as compared to standard IC dice. Rad Hard dice are susceptible to surface damage due to the absence of silicon nitride passivation that is present on most standard dice. Silicon nitride protects the dice surface from scratches by its hard and dense properties. The passivation on Analog Devices Rad Hard dice is silicon dioxide which is much "softer" than silicon nitride. During the visual and preparation for shipment, ESD safe Tweezers are used and only the edge of the die are touched.

ADI recommends that dice handling be performed with extreme care so as to protect the die surface from scratches. If the need arises to move the die in or out of the chip shipment tray (waffle pack), use an ESD-Safe-Plastic-tipped Bent Metal Vacuum Probe, preferably .020" OD x .010" ID (for use with tiny parts). The wand should be compatible with continuous air vacuums. The tip material should be static dissipative Delrin (or equivalent) plastic.

During die attach, care must be exercised to ensure no tweezers, or other equipment, touch the top of the dice.

3.4 The Absolute Maximum Ratings:

Supply Voltage	+22V
Differential Input Voltage	+30V
Input Voltage (Note 1/)	+15V
Output Short Circuit Duration (Note 2/)	Indefinite
Operating Temperature Range	-55°C to 125°C
Maximum Junction Temperature	150°C
Storage Temperature Range	-65°C to 150°C
Lead Temperature (Soldering, 10 sec.)	300°C

NOTE 1/: For supply voltages less than $\pm 15V$, the maximum input voltage is equal to the supply voltage.

NOTE 2/: The output may be shorted to ground or either power supply indefinitely, provided the case Temperature is below 125°C.

3.5 Design, Construction, and Physical Dimensions: Detail design, construction, physical dimensions, and electrical requirements shall be specified herein.

3.6 Outline Dimensions and Pad Functions: Dice outline dimensions, pad functions, and locations shall be specified in **Figure 1**.

3.7 Radiation Hardness Assurance (RHA):

3.7.1 The manufacturer shall perform a lot sample test as an internal process monitor for total dose radiation tolerance. The sample test is performed with MIL-STD-883 TM1019 Condition A as a guideline.

3.7.2 For guaranteed radiation performance to MIL-STD-883, Method 1019, total dose irradiation, the manufacturer will provide certified RAD testing and report through an independent test laboratory when required as a customer purchase order line item.

3.7.3 Total dose bias circuit is specified in **Figure 2**.

3.8 Wafer (or Dice) Probe: Dice shall be 100% probed at $T_a = +25^\circ\text{C}$ to the limits shown in **Table I** herein. All reject dice shall be removed from the lot. This testing is normally performed prior to dicing the wafer into chips. Final specifications after assembly are sample tested during the element evaluation.

3.9 Wafer Lot Acceptance: Wafer lot acceptance shall be in accordance with MIL-PRF-38535, Appendix A, except for the following: Top side glassivation thickness shall be a **minimum of 4KÅ**.

3.10 Wafer Lot Acceptance Report: SEM is performed per MIL-STD-883, Method 2018. Copies of SEM photographs shall be supplied with the Wafer Lot Acceptance Report as part of a Space Data Pack when specified as a customer purchase order line item.

3.11 Traceability: Wafer Diffusion Lot and Wafer traceability shall be maintained through Quality Conformance Inspection.

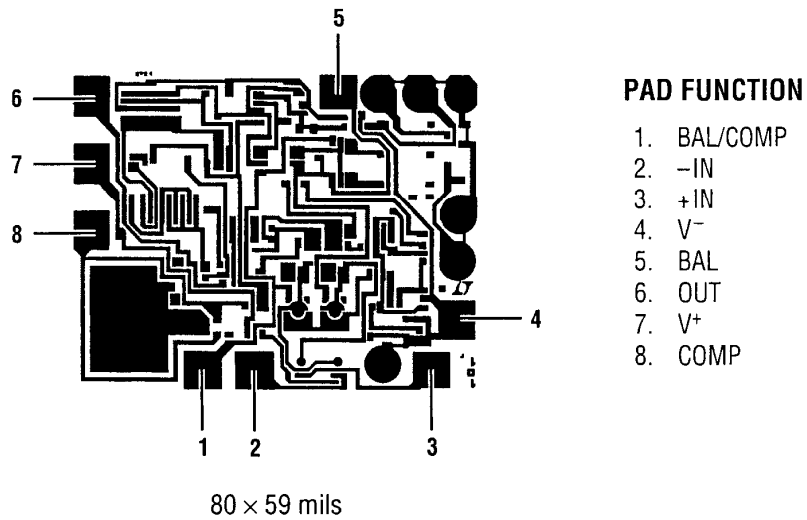
4.0 QUALITY CONFORMANCE INSPECTION: Quality Conformance Inspection shall consist of the tests and inspections specified herein.

- 5.0 SAMPLE ELEMENT EVALUATION: A sample from **each wafer supplying dice** shall be assembled and subjected to element evaluation per **Table III** herein.
- 5.1 100 Percent Visual Inspection: All dice supplied to this specification shall be inspected in accordance with MIL-STD-883, Method 2010, Condition A. All reject dice shall be removed from the lot.
- 5.2 Electrical Performance Characteristics for Element Evaluation: The electrical performance characteristics shall be as specified in **Table I** and **Table II** herein.
- 5.3 Sample Testing: Each wafer supplying dice for delivery to this specification shall be subjected to element evaluation sample testing. No dice shall be delivered until all the lot sample testing has been performed and the results found to be acceptable unless the customer supplies a written approval for shipment prior to completion of wafer qualification as specified in this specification.
- 5.4 Part Marking of Element Evaluation Sample Includes:
- 5.4.1 LTC Logo
- 5.4.2 LTC Part Number
- 5.4.3 Date Code
- 5.4.4 Serial Number
- 5.4.5 ESD Identifier per MIL-PRF-38535, Appendix A
- 5.4.6 Diffusion Lot Number
- 5.4.7 Wafer Number
- 5.5 Burn-In Requirement: Burn-In circuit for TO5 package is specified in **Figure 3**.
- 5.6 Mechanical/Packaging Requirements: Case Outline and Dimensions are in accordance with **Figure 4**.
- 5.7 Terminal Connections: The terminal connections shall be as specified in **Figure 5**.
- 5.8 Lead Material and Finish: The lead material and finish shall be Kovar with hot solder dip (Finish letter A) in accordance with MIL-PRF-38535.
- 6.0 VERIFICATION (QUALITY ASSURANCE PROVISIONS)
- 6.1 Quality Assurance Provisions: Quality Assurance provisions shall be in accordance with MIL-PRF-38535. Analog Devices is a QML certified company and all Rad Hard candidates are assembled on qualified Class S manufacturing lines.
- 6.2 Sampling and Inspection: Sampling and Inspection shall be in accordance with **Table III** herein.
- 6.3 Screening: Screening requirements shall be in accordance with **Table III** herein.
- 6.4 Deliverable Data: Deliverable data that will ship with devices when a Space Data Pack is ordered:

- 6.4.1 Lot Serial Number Sheets identifying all Canned Sample devices accepted through final inspection by serial number.
- 6.4.2 100% attributes (completed element evaluation traveler).
- 6.4.3 Element Evaluation variables data, including Burn-In and Op Life
- 6.4.4 SEM photographs (3.10 herein)
- 6.4.5 Wafer Lot Acceptance Report (3.9 herein)
- 6.4.6 A copy of outside test laboratory radiation report if ordered
- 6.4.7 Certificate of Conformance certifying that the devices meet all the requirements of this specification and have successfully completed the mandatory tests and inspections herein.

Note: Items 6. 4.1 and 6. 4.7 will be delivered as a minimum, with each shipment.

- 7.0 Packaging Requirements: Packaging shall be in accordance with Appendix A of MIL-PRF-38535. All dice shall be packaged in multicavity containers composed of conductive, anti-static, or static dissipative material with an external conductive field shielding barrier.

DICE OUTLINE DIMENSIONS AND PAD FUNCTIONS

Backside (substrate) is an alloyed gold layer. May be connected to V⁻ or no connection.

FIGURE 1

TOTAL DOSE BIAS CIRCUIT

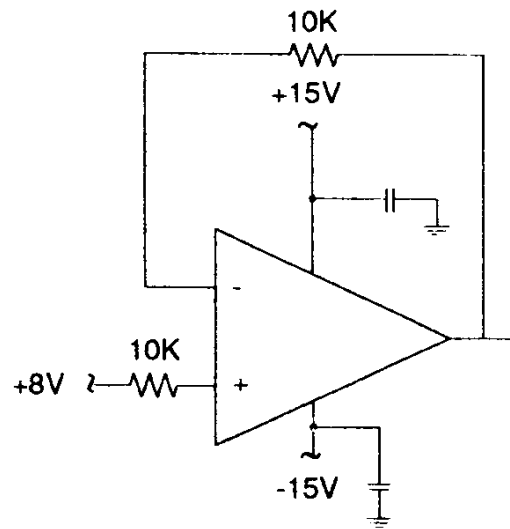
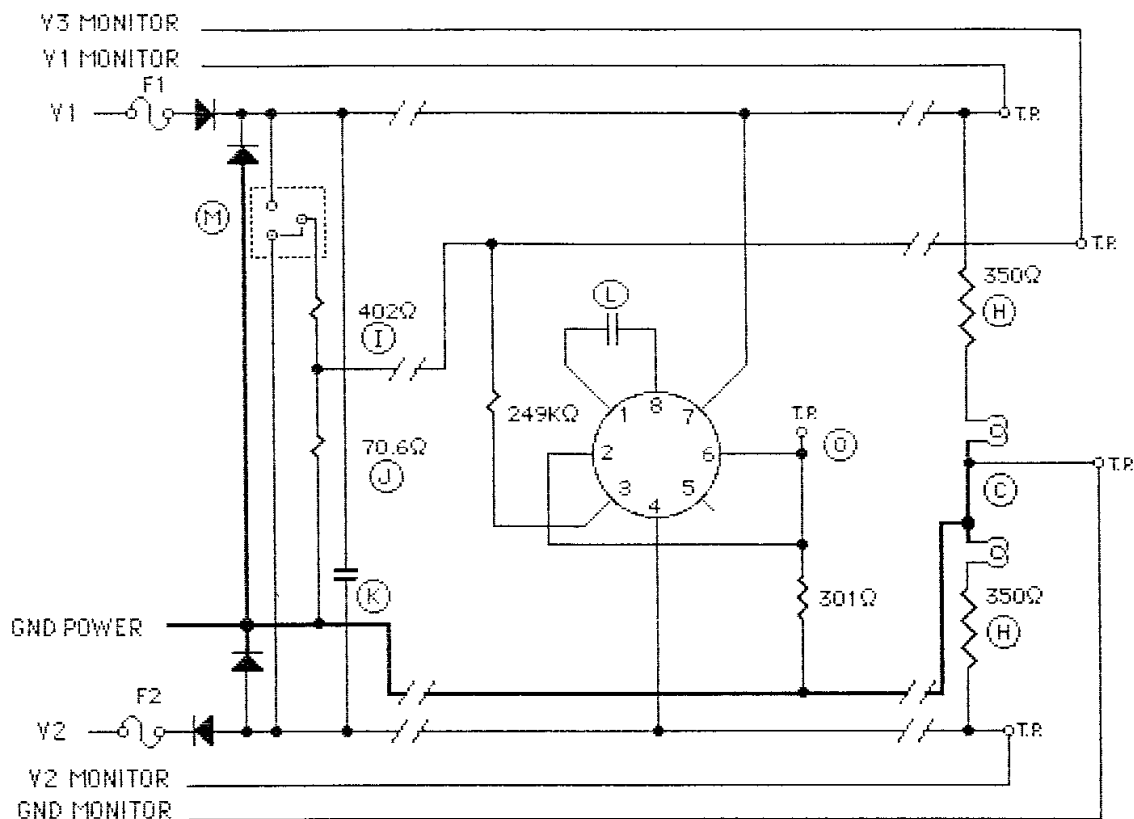


FIGURE 2

BURN-IN CIRCUIT



NOTES:

1. Unless otherwise specified, component tolerances shall be per military specification.
2. $T_j = 191.7^\circ\text{C}$ maximum at 150°C ambient.
3. $T_j = 166.7^\circ\text{C}$ maximum at 125°C ambient.
4. Burn-in Voltages: $V_1 = +20\text{V}$ to $+22\text{V}$
 $V_2 = -20\text{V}$ to -22V
 $V_3 = -3\text{V}$ to -3.3V MONITOR ONLY

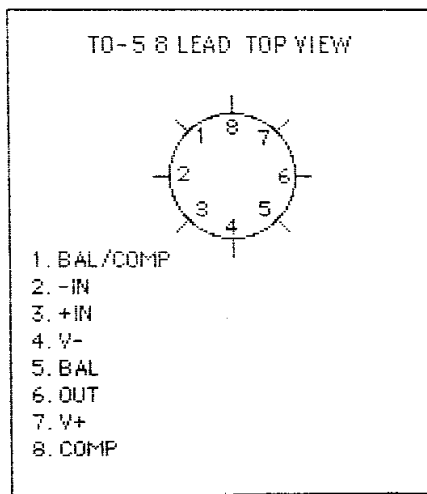
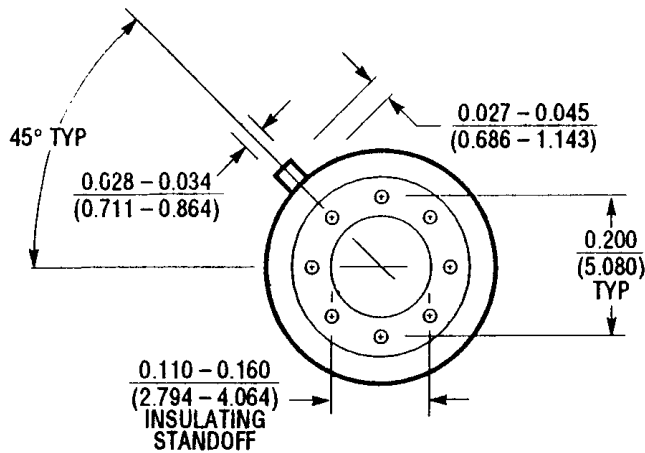
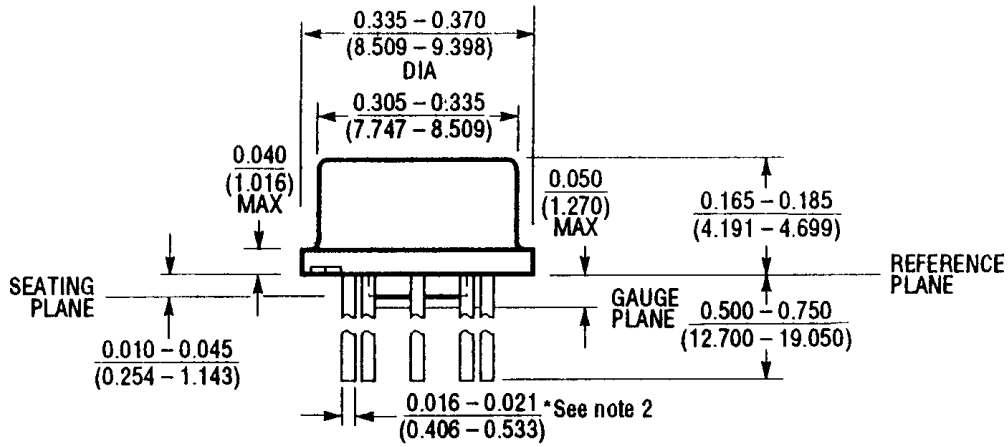


FIGURE 3

TO5, 8 LEADS, CASE OUTLINE



NOTE: 1. LEAD DIAMETER IS UNCONTROLLED BETWEEN THE REFERENCE PLANE AND SEATING PLANE.

2. FOR SOLDER DIP LEAD FINISH, LEAD DIAMETER IS $\frac{0.016 - 0.024}{(0.406 - 0.610)}$

$\theta_{ja} = +150^{\circ}\text{C/W}$
 $\theta_{jc} = +40^{\circ}\text{C/W}$

FIGURE 4

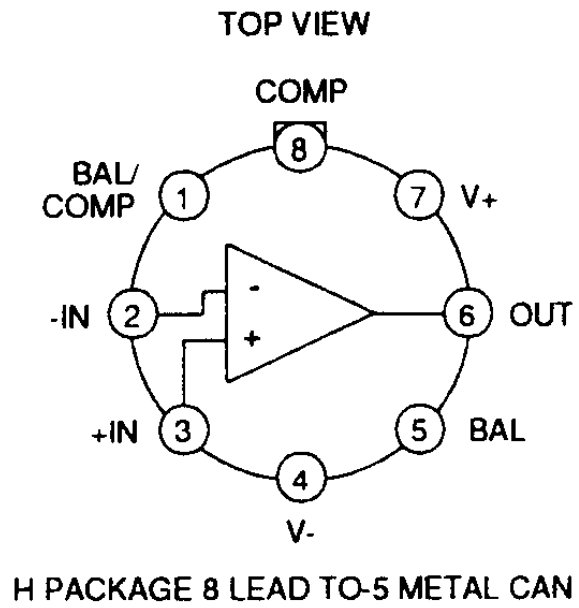
TERMINAL CONNECTIONS**FIGURE 5**

TABLE I DICE ELECTRICAL CHARACTERISTICS – Element Evaluation $T_A = 25^\circ\text{C}$. $V_S = \pm 20\text{V}$ unless otherwise noted.

SYMBOL	PARAMETER	CONDITIONS	$T_A = 25^\circ\text{C}$		UNITS
			MIN	MAX	
Pre-Irradiation (Note 1)					
V_{OS}	Input Offset Voltage	$R_S \leq 50\text{k}$		2	mV
I_{OS}	Input Offset Current			10	nA
I_B	Input Bias Current	$V_{CM} = 0\text{V}$		75	nA
A_{VOL}	Large Signal Voltage Gain	$V_S = \pm 15\text{V}$, $V_{OUT} = \pm 10\text{V}$, $R_L \geq 2\text{k}$	50		V/mV
CMRR	Common Mode Rejection Ratio	$R_S \leq 50\text{k}$	80		dB
PSRR	Power Supply Rejection Ratio	$R_S \leq 50\text{k}$	80		dB
	Input Voltage Range	$V_S = \pm 20\text{V}$	± 15		V
V_{OUT}	Output Voltage Swing	$V_S = \pm 15\text{V}$, $R_L \geq 10\text{k}$ $V_S = \pm 15\text{V}$, $R_L \geq 2\text{k}$	± 12 ± 10		V V
I_S	Supply Current	$V_S = \pm 20\text{V}$		3	mA

TABLE II ELECTRICAL CHARACTERISTICS – Post-Irradiation $T_A = 25^\circ\text{C}$. $V_S = \pm 20\text{V}$ unless otherwise noted.

SYMBOL	PARAMETER	CONDITIONS	10Krad(SI)		20Krad(SI)		50Krad(SI)		100Krad(SI)		200Krad(SI)		UNITS
			MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	
Post-Irradiation (Note 4)													
V_{OS}	Input Offset Voltage	$R_S \leq 50\text{k}$	2		2		2		2		3		mV
I_{OS}	Input Offset Current		10		10		10		10		20		nA
I_B	Input Bias Current		75		75		100		200		400		nA
CMRR	Common Mode Rejection Ratio	$V_{CM} = \pm 15\text{V}$, $R_S \leq 50\text{k}$	80		80		80		80		80		dB
PSRR	Power Supply Rejection Ratio	$V_{CM} = \pm 5\text{V}$ to $\pm 20\text{V}$, $R_S \leq 50\text{k}$	80		80		80		80		80		dB
A_{VOL}	Large Signal Voltage Gain	$R_L = \pm 2\text{k}$, $V_O = \pm 10\text{V}$, $V_S = \pm 15\text{V}$	50		50		50		50		25		V/mV
V_{OUT}	Maximum Output Voltage Swing	$V_S = \pm 15\text{V}$, $R_L \geq 10\text{k}$ $V_S = \pm 15\text{V}$, $R_L \geq 2\text{k}$	± 12 ± 10		± 12 ± 10		± 12 ± 10		± 12 ± 10		± 12 ± 10		V V
I_S	Supply Current	$V_S = \pm 20\text{V}$	3		3		3		3		3		mA

Note 1: Unless otherwise noted, all measurements are made with unity gain compensation ($C_1 = 30\text{pF}$); these specifications apply for $\pm 5\text{V} \leq V_S \leq 20\text{V}$.

Note 2: For supply voltages less than $\pm 15\text{V}$, the maximum input voltage is equal to the supply voltage.

Note 3: Refer to LTC standard product data sheet for all other applicable information.

Note 4: The post-irradiation table is for lot qualification based on sample lot assembly and testing only. Contact LTC marketing for more detail.



RH CANNED SAMPLE TABLE FOR QUALIFYING DICE SALES

TABLE III RH ELEMENT EVALUATION TABLE QUALIFICATION OF DICE SALES

SUBGROUP	CLASS			OPERATION	MIL-STD-883 METHOD	CONDITION	QUANTITY (ACCEPT NUMBER)
	K/S	V	H/B				
1	X	X		SEM	2018	N/A	REF: METHOD 2018 FOR S/S
2	X	X	X	ELEMENT ELECTRICAL (WAFER SORT @ 25°C)			100%
3	X	X	X	ELEMENT VISUAL (2nd OP)	2010	A	100%
4	X	X	X	INTERNAL VISUAL (3rd OP)	2010	A	ASSEMBLED PARTS ONLY
	X	X		DIE SHEAR MONITOR	2019		
5	X	X		BOND PULL MONITOR	2011		ASSEMBLED PARTS ONLY
	X	X		STABILIZATION BAKE	1008	C	
	X	X		TEMPERATURE CYCLE	1010	C	
	X	X		CONSTANT ACCELERATION	2001	E	
	X	X		FINE LEAK	1014	A	
6	X	X		GROSS LEAK	1014	C	45(0)
	X	X		FIRST ROOM ELECTRICAL - READ & RECORD (REPLACE ANY ASSEMBLY-RELATED REJECTS)			
	X	X		PRE BURN-IN/ELECT. READ & RECORD @ +125°C or +150°C, -55°C			
	X	X		BURN-IN: +125°C/240 hrs. or +150°C/120 hrs.	1015	+ 125°C MINIMUM 240 HOURS	
	X	X		POST BURN-IN/ELECT. READ & RECORD @ 25°C			
	X	X		POST BURN-IN/ELECT. READ & RECORD @ +125°C or +150°C, -55°C			
7	X	X		TOTAL IRRADIATION DOSE	1019	A	15(0) OR 25(1) - # of wires
	X	X		PRE OP-LIFE ELECTRICAL @ 25°C READ & RECORD			
	X	X		OPERATING LIFE: +125°C/1000 hrs. or +150°C/500 hrs.	1005	+ 125°C MINIMUM 1000 HOURS	
	X	X		POST OP-LIFE ELECT. (R & R @ 25°C, +125°C OR +150°C, -55°C)			

NOTE: LTC is not qualified to process to MIL-PRF-38534. This is an LTC imposed element evaluation that follows MIL-STD-883 test methods and conditions. Please note the quantity and accept number from Sample Size Series of 5%, accept on 0, and note that the actual sample and accept number does not begin until Subgroup 6 OP-LIFE.

NOTE: Tests within Subgroup 5 may be performed in any sequence.

NOTE: LTC's radiation tolerance (RH) die has a topside glassivation thickness of 4KA minimum.

NOTE: Sample sizes on the travelers may be larger than that indicated in the above table; however, the larger sample size is to accommodate extra units for replacement devices in the event of equipment or operator error and for assembly related rejects in Subgroup 6, and for Wire Bond Evaluation, Subgroup 7. The larger sample size is at all times kept segregated and, if used for qualification, has all the required processing imposed.